Features
- Broadband Performance, 26 to 40 GHz
- Low Loss <1 dB
- High Isolation >38 dB
- Up to 13 W CW Power, +85°C
- Die with G-S-G RF Pads and DC Bias Pads
- Includes DC Blocks and RF Bias Networks
- 23 dBm power handling in terminated port

Description
The MASW-011036 is a high power SPDT with 50 Ω terminated RF ports. This broadband, high linearity, SPDT switch was developed for Ka–Band applications that require up to 13 Watts CW power handling at an environmental temperature of +85°C while maintaining low insertion loss and high isolation.

The SPDT MMIC utilizes MACOM’s proven AlGaAs PIN diode technology. The switch is fully passivated with silicon nitride and has an added polymer layer for scratch protection. The protective coating prevents damage to the junction and the anode air-bridge during handling and assembly. The die has backside metallization to facilitate an epoxy die attach process.

Functional Diagram

Pin Configuration:
(Back Metal is RF, DC, and Thermal Ground)

<table>
<thead>
<tr>
<th>Pin #</th>
<th>Function</th>
</tr>
</thead>
<tbody>
<tr>
<td>1</td>
<td>RFCOMMON</td>
</tr>
<tr>
<td>2</td>
<td>BIAS 1</td>
</tr>
<tr>
<td>3</td>
<td>RF1</td>
</tr>
<tr>
<td>4</td>
<td>RF2</td>
</tr>
<tr>
<td>5</td>
<td>BIAS 2</td>
</tr>
</tbody>
</table>

Ordering Information

<table>
<thead>
<tr>
<th>Part Number</th>
<th>Package</th>
</tr>
</thead>
<tbody>
<tr>
<td>MASW-011036-1413WR</td>
<td>Separated Die on 7” Grip Ring¹, Electronic Map</td>
</tr>
<tr>
<td>MASW-011036-1413RI</td>
<td>Separated Die on 7” Grip Ring¹, Inked Wafer</td>
</tr>
<tr>
<td>MASW-011036-14130G</td>
<td>Die in Gel Pack¹</td>
</tr>
<tr>
<td>MASW-011036-001SMB</td>
<td>Sample Evaluation Board</td>
</tr>
</tbody>
</table>

1. Die quantity varies.

**Electrical Specifications:**
Freq. = 28 - 30 GHz, $T_A = +25^\circ$C, +4 V @ +25 mA / -15 V @ 0 mA, $Z_0 = 50 \, \Omega$

<table>
<thead>
<tr>
<th>Parameter</th>
<th>Test Conditions</th>
<th>Units</th>
<th>Min.</th>
<th>Typ.</th>
<th>Max.</th>
</tr>
</thead>
<tbody>
<tr>
<td>Insertion Loss</td>
<td>26 - 28 GHz, 28 - 32 GHz, 32 - 36 GHz, 36 - 40 GHz</td>
<td>dB</td>
<td>—</td>
<td>0.80</td>
<td>1.0</td>
</tr>
<tr>
<td>Isolation$^2$</td>
<td>26 - 28 GHz, 28 - 32 GHz, 32 - 36 GHz, 36 - 40 GHz</td>
<td>dB</td>
<td>—</td>
<td>34</td>
<td>—</td>
</tr>
<tr>
<td>Input / Output Return Loss</td>
<td>On state</td>
<td>26 - 28 GHz, 28 - 32 GHz, 32 - 36 GHz, 36 - 40 GHz</td>
<td>dB</td>
<td>—</td>
<td>13</td>
</tr>
<tr>
<td>RF1, 2 Return Loss, Off state</td>
<td>26 - 28 GHz, 28 - 32 GHz, 32 - 36 GHz, 36 - 40 GHz</td>
<td>dB</td>
<td>—</td>
<td>7.5</td>
<td></td>
</tr>
<tr>
<td>Switching Speed-$T_{ON}$</td>
<td>50% DC to 90% RF</td>
<td>ns</td>
<td>—</td>
<td>30</td>
<td></td>
</tr>
<tr>
<td>Switching Speed-$T_{OFF}$</td>
<td>50% DC to 10% RF</td>
<td>ns</td>
<td>—</td>
<td>21</td>
<td></td>
</tr>
<tr>
<td>Rise Time - $T_{Rise}$</td>
<td>10% to 90% RF</td>
<td>ns</td>
<td>—</td>
<td>10</td>
<td></td>
</tr>
<tr>
<td>Fall Time - $T_{Fall}$</td>
<td>90% to 10% RF</td>
<td>ns</td>
<td>—</td>
<td>8</td>
<td></td>
</tr>
<tr>
<td>CW Input Power$^3$</td>
<td>-25 V @ +85°C</td>
<td>dBm</td>
<td>—</td>
<td>41.2</td>
<td></td>
</tr>
<tr>
<td>Reverse Bias Voltage$^3$</td>
<td>—</td>
<td>V</td>
<td>-32</td>
<td>-15</td>
<td></td>
</tr>
<tr>
<td>Reverse Bias Current$^3$</td>
<td>-15 V</td>
<td>nA</td>
<td>—</td>
<td>25</td>
<td></td>
</tr>
<tr>
<td>Forward Bias Current$^4$</td>
<td>+4 V</td>
<td>mA</td>
<td>—</td>
<td>25</td>
<td></td>
</tr>
</tbody>
</table>

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2. Isolation defined with 1 port in low loss state.
3. Reverse bias voltage should be determined based on working conditions. For example, -25 V @ 41.2 dBm input power. For lower power applications, a less negative voltage can be used. R. Caverly and G. Hiller, "Establishing the Minimum Reverse Bias for a P-i-N Diode in a High Power Switch," IEEE Transactions on Microwave Theory and Techniques, Vol.38, No.12, December 1990.
4. Forward bias voltage should be determined based on working conditions.
### Absolute Maximum Ratings\(^{5,6}\)

<table>
<thead>
<tr>
<th>Parameter</th>
<th>Absolute Maximum</th>
</tr>
</thead>
<tbody>
<tr>
<td>Reverse Bias Voltage</td>
<td>-50 V</td>
</tr>
<tr>
<td>Forward Bias Current</td>
<td>40 mA</td>
</tr>
<tr>
<td>CW Incident Power</td>
<td>43 dBm</td>
</tr>
<tr>
<td>CW Incident Power (Terminated Port)</td>
<td>26 dBm</td>
</tr>
<tr>
<td>Operating Temperature</td>
<td>-40°C to +85°C</td>
</tr>
<tr>
<td>Storage Temperature</td>
<td>-65°C to +150°C</td>
</tr>
</tbody>
</table>

5. Exceeding any one or combination of these limits may cause permanent damage to this device.
6. M/A-COM does not recommend sustained operation near these survivability limits.

### Truth Table\(^{3,4}\)

<table>
<thead>
<tr>
<th>RF(\text{COMMOM}) Path</th>
<th>Bias 1</th>
<th>Bias 2</th>
</tr>
</thead>
<tbody>
<tr>
<td>RF1 Insertion Loss RF2 Isolation</td>
<td>-15 V (0 mA)</td>
<td>+4 V (+25 mA)</td>
</tr>
<tr>
<td>RF2 Insertion Loss RF1 Isolation</td>
<td>+4 V (+25 mA)</td>
<td>-15 V (0 mA)</td>
</tr>
</tbody>
</table>

### Die Outline

Dimensions indicated in μm.
Die Thickness: 100 μm
RF Pads (1, 3, 4): 100 x 200 μm.
DC Bias Pads (2 & 5): 100 x 100 μm.
Meets JEDEC moisture sensitivity level 1 requirements.

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Handling Procedures

Please observe the following precautions to avoid damage:

### Static Sensitivity

Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these HBM class 1A devices.
Typical Performance @ +25°C

**Insertion Loss (On State)**

- **RF\textsubscript{COMMON} Return Loss (On State)**
- **RF\textsubscript{1, 2} Return Loss (On State)**
- **Isolation (Off State)**
- **RF\textsubscript{1, 2} Return Loss (Off State)**
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